



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

16 A

Features

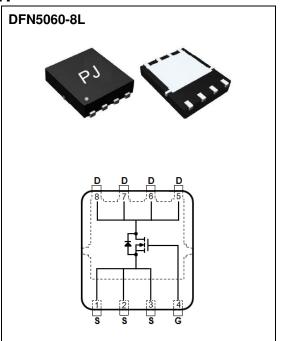
- $R_{DS(ON)}$, V_{GS} @10V, I_D @8A<50m Ω
- $R_{DS(ON)}$, V_{GS} @4.5V, I_{D} @4A<60m Ω
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	60	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	I _D	16		
	T _C =100°C		10	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	64		
Power Dissipation	T _C =25°C	Po	32.6	147	
	T _C =100°C		16.3	W	
Continuous Drain Current (Note 4)	T _A =25°C	I _D	4.4		
	T _A =70°C		3.5	Α	
Power Dissipation	T _A =25°C	Po	2.4	W	
	T _A =70°C		1.6		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	11	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	4.6	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1	1.77	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =10V, I_D =8A	-	37	50	mΩ
		V_{GS} =4.5V, I_D =4A	-	42	60	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_{g}	V_{DS} =30V, I_{D} =4A, V_{GS} =10V (Note 2,3)	-	14	-	nC
Gate-Source Charge	Q_{gs}		-	2.9	-	
Gate-Drain Charge	Q_{gd}		-	2.3	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	815	-	pF
Output Capacitance	Coss		-	379	-	
Reverse Transfer Capacitance	Crss	I=IIVIMZ	-	110	-	
Turn-On Delay Time	td _(on))/ 00\/ l	-	3.9	-	ns
Turn-On Rise Time	t _r	V_{DD} =30V, I_{D} =1A, V_{GS} =10V, R_{G} =3.3 Ω (Note 2.3)	-	13	-	
Turn-Off Delay Time	td _(off)		-	23	-	
Turn-Off Fall Time	t _f		-	6.7	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	,				16	Α
Diode Forward Current	I _S		-	-	10	A
Diode Forward Voltage	V_{SD}	I _S =1A, V _{GS} =0V	-	0.73	1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =15A, V_{DD} =25V, V_{GS} =10V.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

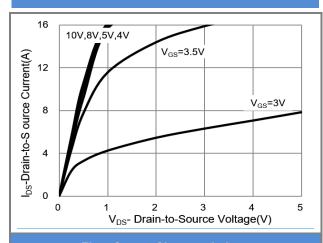


Fig.1 Output Characteristics

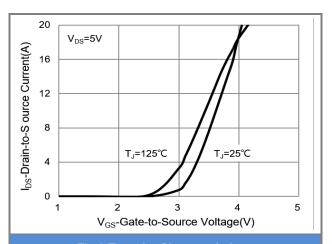


Fig.2 Transfer Characteristics

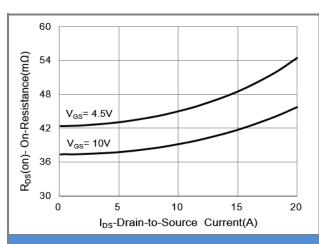


Fig.3 On-Resistance vs. Drain Current

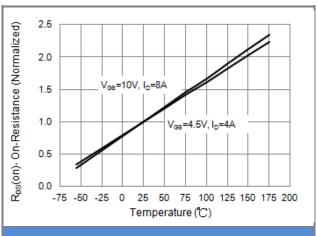
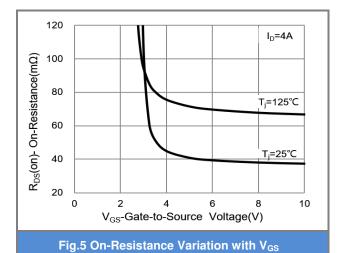


Fig.4 On-Resistance vs. Junction temperature



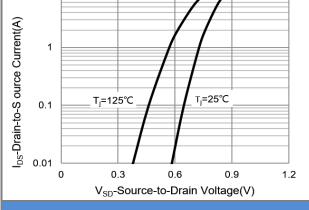


Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

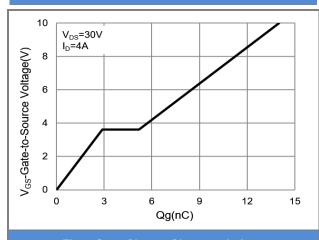


Fig.7 Gate-Charge Characteristics

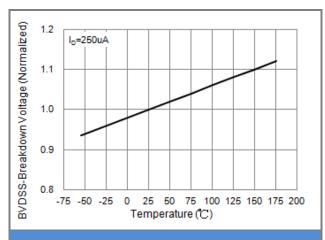


Fig.8 Breakdown Voltage Variation vs. Temperature

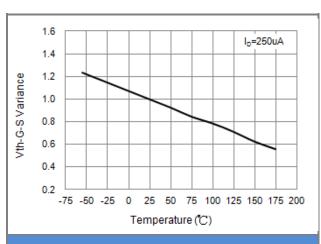


Fig.9 Threshold Voltage Variation with Temperature

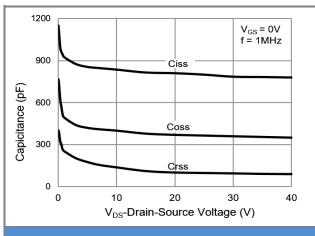
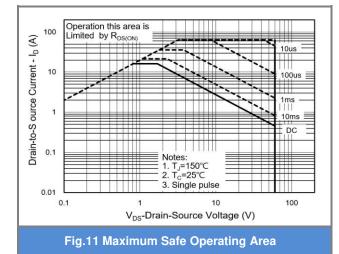


Fig.10 Capacitance vs. Drain-Source Voltage



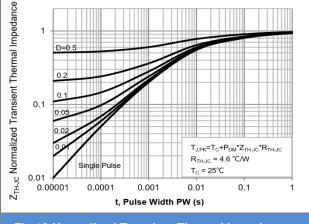


Fig.12 Normalized Transient Thermal Impedance

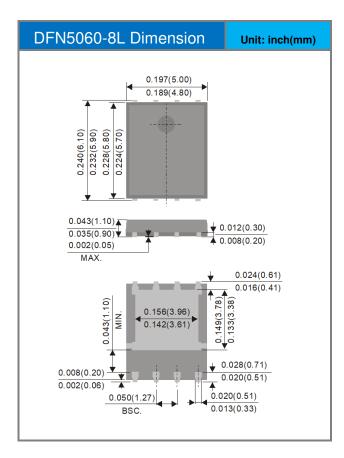


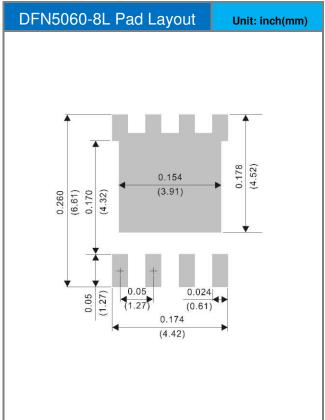


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5458A-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5458A	Halogen free	

Packaging Information & Mounting Pad Layout









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